



May 2001

**QFET™**

# FQPF30N06L

## 60V LOGIC N-Channel MOSFET

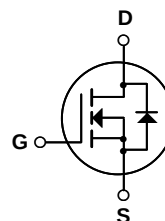
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as automotive, DC/DC converters, and high efficiency switching for power management in portable and battery operated products.

### Features

- 22.5A, 60V,  $R_{DS(on)} = 0.035\Omega$  @  $V_{GS} = 10V$
- Low gate charge ( typical 15 nC)
- Low  $C_{rss}$  ( typical 50 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter                                                                                             | FQPF30N06L  | Units |
|----------------|-------------------------------------------------------------------------------------------------------|-------------|-------|
| $V_{DSS}$      | Drain-Source Voltage                                                                                  | 60          | V     |
| $I_D$          | Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )<br>- Continuous ( $T_C = 100^\circ\text{C}$ ) | 22.5        | A     |
|                |                                                                                                       | 15.9        | A     |
| $I_{DM}$       | Drain Current - Pulsed (Note 1)                                                                       | 90          | A     |
| $V_{GSS}$      | Gate-Source Voltage                                                                                   | $\pm 20$    | V     |
| $E_{AS}$       | Single Pulsed Avalanche Energy (Note 2)                                                               | 350         | mJ    |
| $I_{AR}$       | Avalanche Current (Note 1)                                                                            | 22.5        | A     |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)                                                                  | 3.8         | mJ    |
| dv/dt          | Peak Diode Recovery dv/dt (Note 3)                                                                    | 7.0         | V/ns  |
| $P_D$          | Power Dissipation ( $T_C = 25^\circ\text{C}$ )<br>- Derate above $25^\circ\text{C}$                   | 38          | W     |
|                |                                                                                                       | 0.25        | W/°C  |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range                                                      | -55 to +175 | °C    |
| $T_L$          | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds                         | 300         | °C    |

### Thermal Characteristics

| Symbol          | Parameter                               | Typ | Max  | Units |
|-----------------|-----------------------------------------|-----|------|-------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case    | --  | 3.9  | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | --  | 62.5 | °C/W  |

**Electrical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

**Off Characteristics**

|                                |                                           |                                                                   |    |      |      |                     |
|--------------------------------|-------------------------------------------|-------------------------------------------------------------------|----|------|------|---------------------|
| $BV_{DSS}$                     | Drain-Source Breakdown Voltage            | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$               | 60 | --   | --   | V                   |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$ | -- | 0.06 | --   | V/ $^\circ\text{C}$ |
| $I_{DSS}$                      | Zero Gate Voltage Drain Current           | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$                       | -- | --   | 1    | $\mu\text{A}$       |
|                                |                                           | $V_{DS} = 48\text{ V}, T_C = 150^\circ\text{C}$                   | -- | --   | 10   | $\mu\text{A}$       |
| $I_{GSSF}$                     | Gate-Body Leakage Current, Forward        | $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$                       | -- | --   | 100  | nA                  |
| $I_{GSSR}$                     | Gate-Body Leakage Current, Reverse        | $V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$                      | -- | --   | -100 | nA                  |

**On Characteristics**

|              |                                   |                                                      |     |       |       |          |
|--------------|-----------------------------------|------------------------------------------------------|-----|-------|-------|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$      | 1.0 | --    | 2.5   | V        |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = 10\text{ V}, I_D = 11.3\text{ A}$          | --  | 0.027 | 0.035 | $\Omega$ |
|              |                                   | $V_{GS} = 5\text{ V}, I_D = 11.3\text{ A}$           | --  | 0.035 | 0.045 | $\Omega$ |
| $g_{FS}$     | Forward Transconductance          | $V_{DS} = 25\text{ V}, I_D = 11.3\text{ A}$ (Note 4) | --  | 22    | --    | S        |

**Dynamic Characteristics**

|           |                              |                                                                      |    |     |      |    |
|-----------|------------------------------|----------------------------------------------------------------------|----|-----|------|----|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$<br>$f = 1.0\text{ MHz}$ | -- | 800 | 1040 | pF |
| $C_{oss}$ | Output Capacitance           |                                                                      | -- | 270 | 350  | pF |
| $C_{rss}$ | Reverse Transfer Capacitance |                                                                      | -- | 50  | 65   | pF |

**Switching Characteristics**

|              |                     |                                                                                       |    |     |     |    |
|--------------|---------------------|---------------------------------------------------------------------------------------|----|-----|-----|----|
| $t_{d(on)}$  | Turn-On Delay Time  | $V_{DD} = 30\text{ V}, I_D = 16\text{ A},$<br>$R_G = 25\text{ }\Omega$<br>(Note 4, 5) | -- | 15  | 40  | ns |
| $t_r$        | Turn-On Rise Time   |                                                                                       | -- | 210 | 430 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time |                                                                                       | -- | 60  | 130 | ns |
| $t_f$        | Turn-Off Fall Time  |                                                                                       | -- | 110 | 230 | ns |
| $Q_g$        | Total Gate Charge   | $V_{DS} = 48\text{ V}, I_D = 32\text{ A},$<br>$V_{GS} = 5\text{ V}$<br>(Note 4, 5)    | -- | 15  | 20  | nC |
| $Q_{gs}$     | Gate-Source Charge  |                                                                                       | -- | 3.5 | --  | nC |
| $Q_{gd}$     | Gate-Drain Charge   |                                                                                       | -- | 8.5 | --  | nC |

**Drain-Source Diode Characteristics and Maximum Ratings**

|                 |                                                       |                                                |    |    |      |    |
|-----------------|-------------------------------------------------------|------------------------------------------------|----|----|------|----|
| I <sub>S</sub>  | Maximum Continuous Drain-Source Diode Forward Current |                                                | -- | -- | 22.5 | A  |
| I <sub>SM</sub> | Maximum Pulsed Drain-Source Diode Forward Current     |                                                | -- | -- | 90   | A  |
| V <sub>SD</sub> | Drain-Source Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 22.5 A | -- | -- | 1.5  | V  |
| t <sub>rr</sub> | Reverse Recovery Time                                 | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 32 A,  | -- | 60 | --   | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                               | dI <sub>F</sub> / dt = 100 A/μs (Note 4)       | -- | 90 | --   | nC |

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 810\text{ }\mu\text{H}$ ,  $I_{AS} = 22.5\text{ A}$ ,  $V_{DD} = 25\text{ V}$ ,  $R_G = 25\text{ }\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 32\text{ A}$ ,  $di/dt \leq 300\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\text{ }\mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

## Typical Characteristics

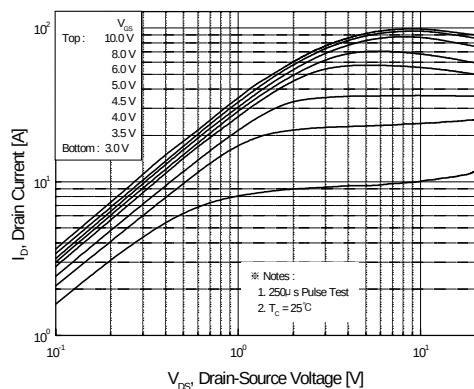


Figure 1. On-Region Characteristics

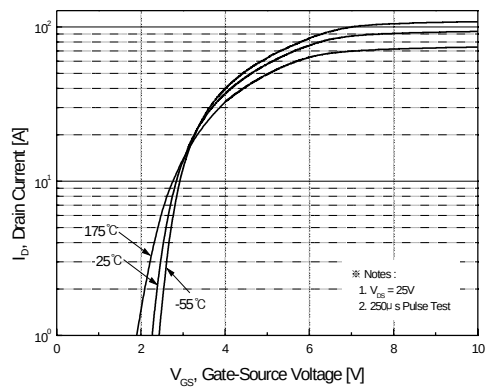


Figure 2. Transfer Characteristics

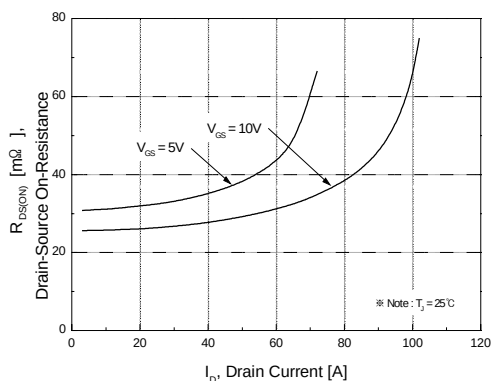


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

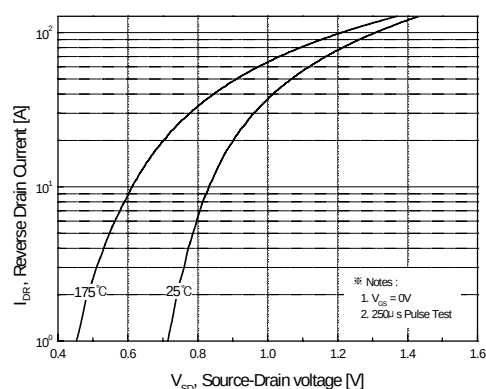


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

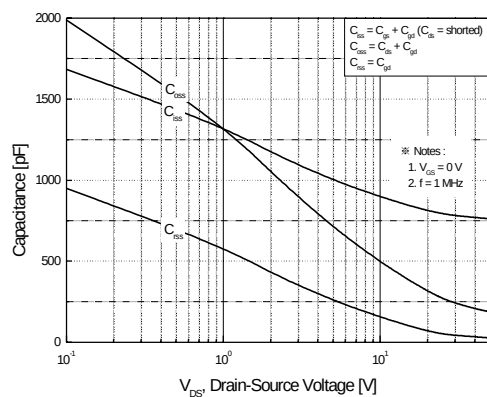


Figure 5. Capacitance Characteristics

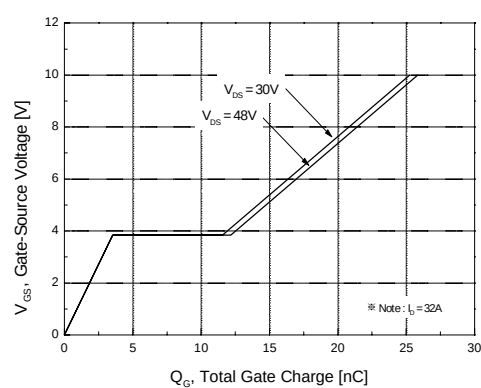
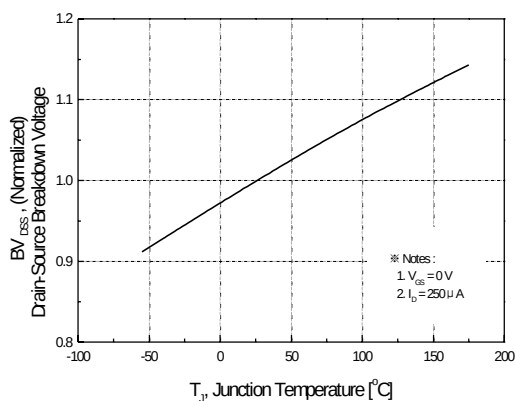
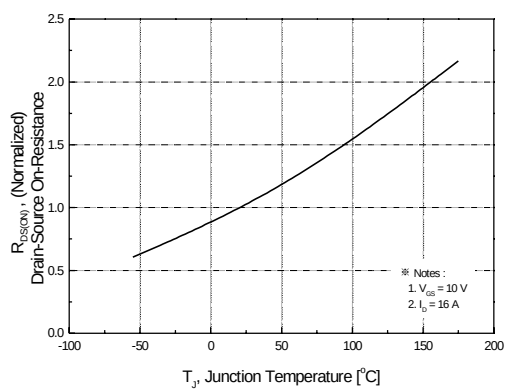


Figure 6. Gate Charge Characteristics

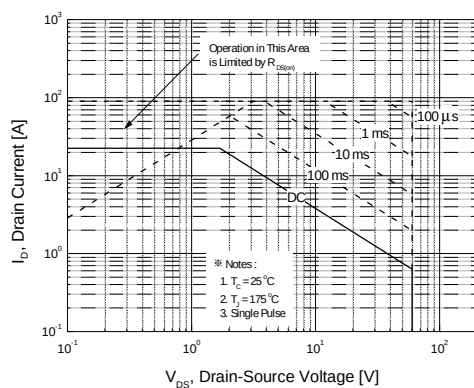
# Typical Characteristics (Continued)



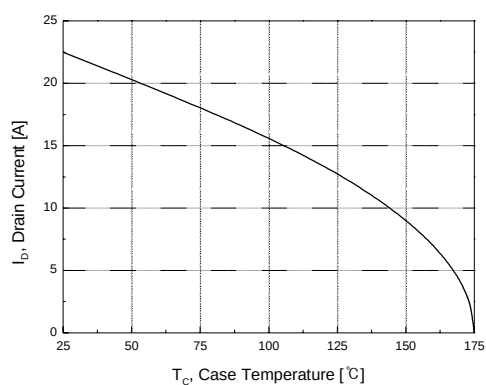
**Figure 7. Breakdown Voltage Variation vs. Temperature**



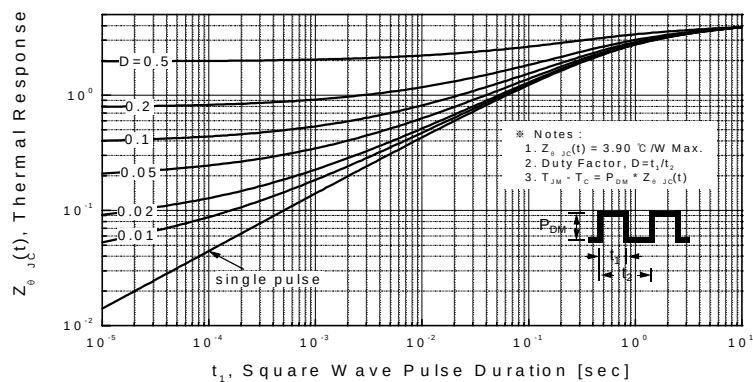
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**

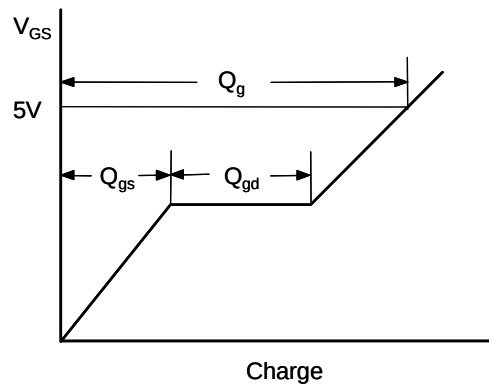
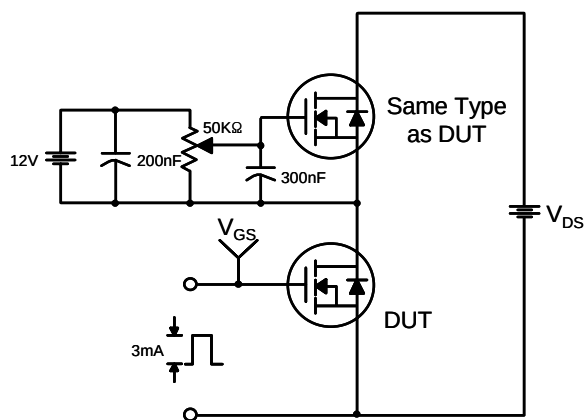


**Figure 10. Maximum Drain Current vs. Case Temperature**

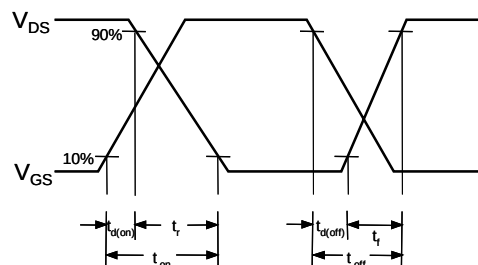
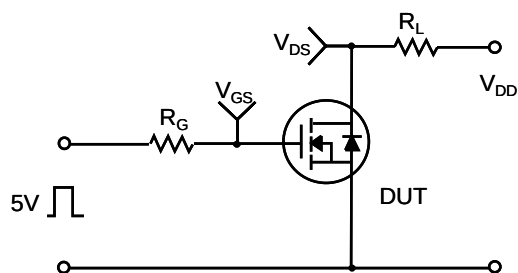


**Figure 11. Transient Thermal Response Curve**

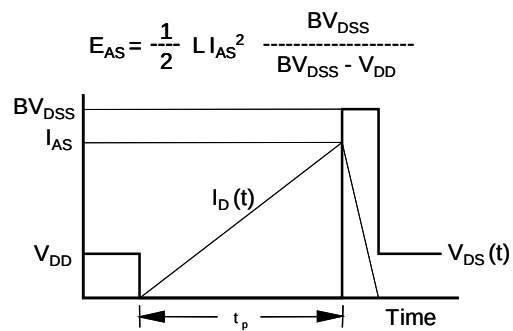
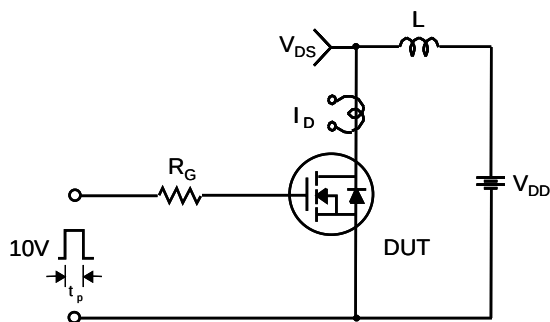
## Gate Charge Test Circuit &amp; Waveform

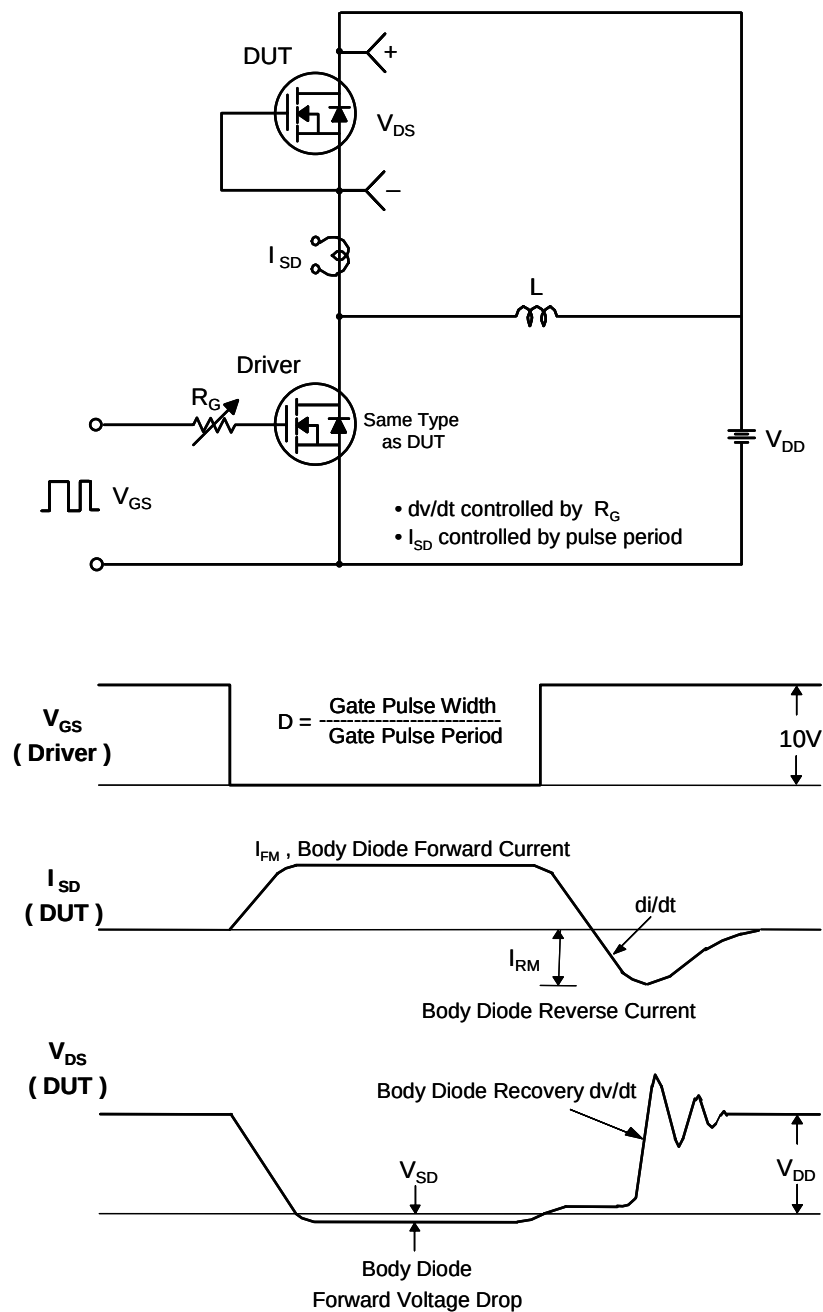


## Resistive Switching Test Circuit &amp; Waveforms



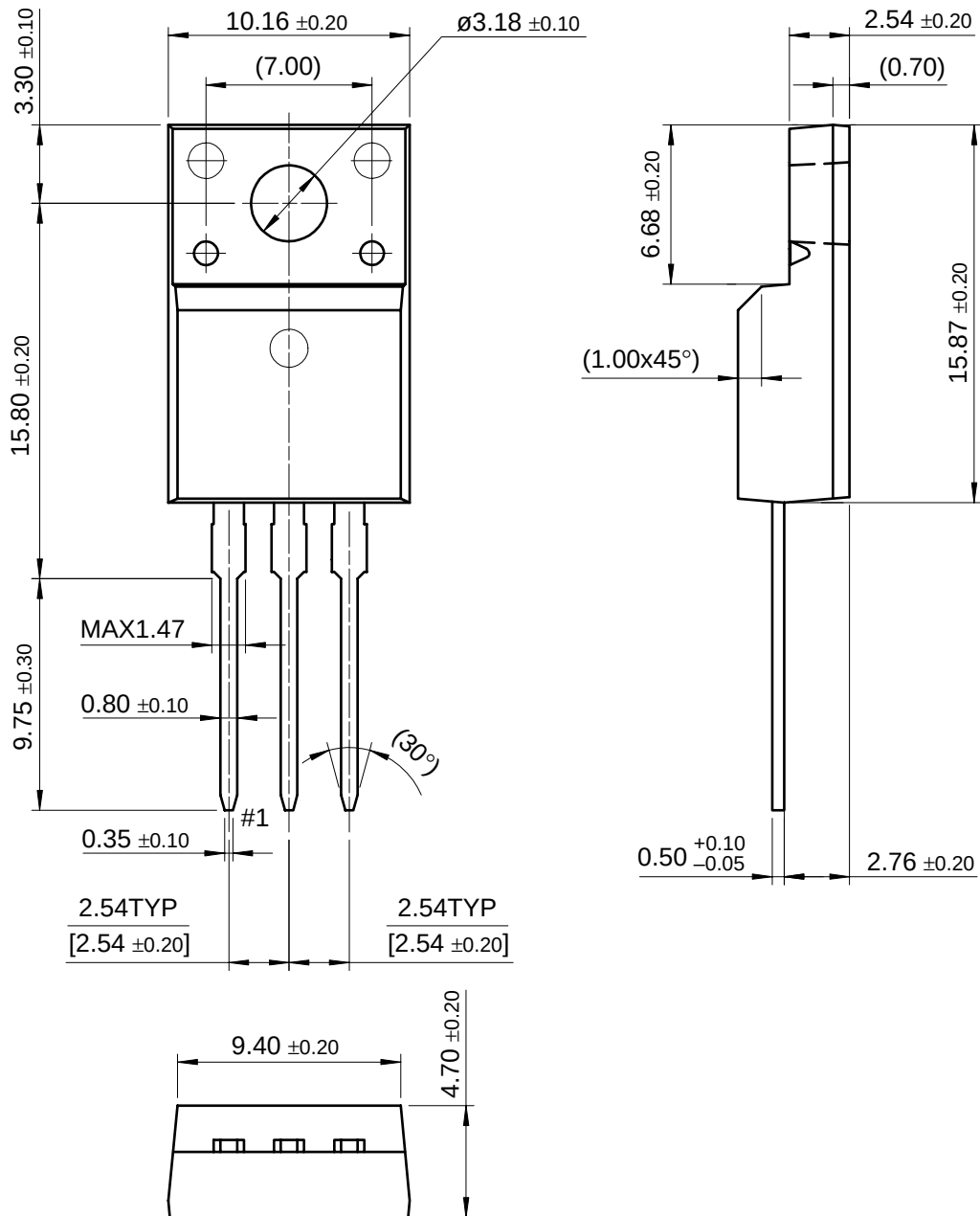
## Unclamped Inductive Switching Test Circuit &amp; Waveforms



Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

# Package Dimensions

## TO-220F



FQPF30N06L

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